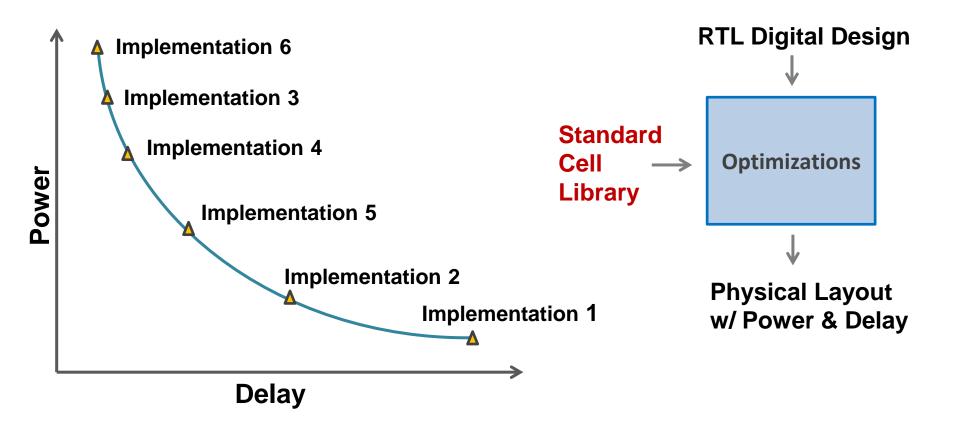


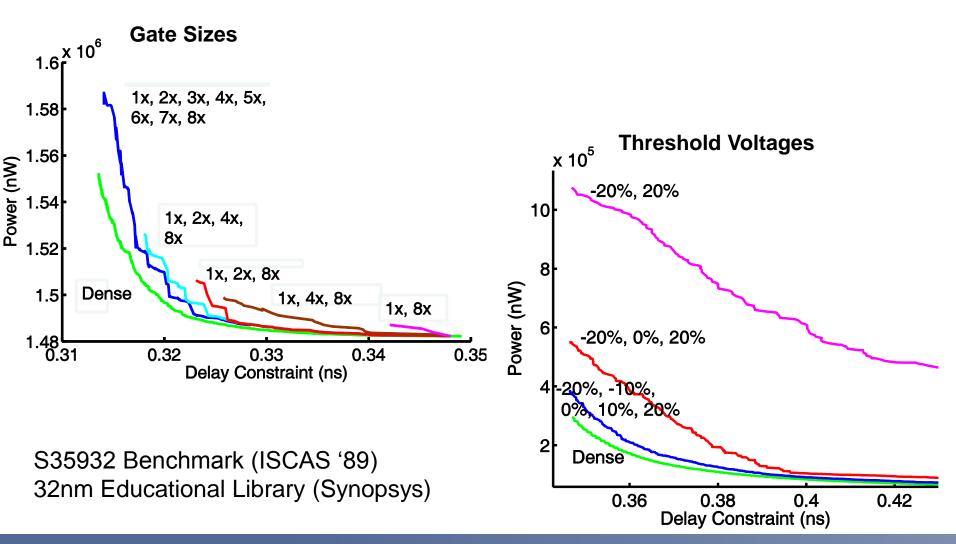
Impact of Range and Precision on Standard Cell Libraries

John Lee Puneet Gupta UCLA Electrical Engineering {lee@ee.ucla.edu, puneet@ee.ucla.edu}

Introduction: Tradeoff Between Power and Delay



Motivation: Power and Delay Tradeoffs



Motivation: FinFET Standard Cell Libraries

- Gate sizes quantized (1x, 2x, 3x, 4x, ...)
 - Affects the delay range and feasibility
- Limited availability of Threshold Voltages
 - Created by adjusting gate workfunction or use the back-gate
 - Number of threshold voltages will likely be limited [Warnock 11]
- What does this mean for resulting designs? How can this impact be quantified?

Outline

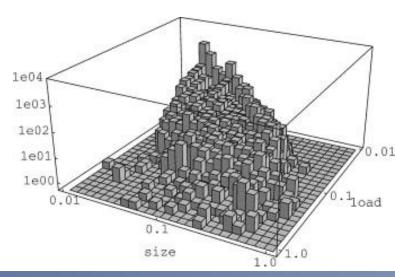
- 1. Prior Approaches to finding the impact of the standard cell library
- 2. Expressions to estimate suboptimality
 - Gate Sizes
 - Threshold Voltages
- 3. Experimental validation
 - Gate sizes
 - Threshold voltages
- 4. Discussion on Range and Precision

Prior Approaches

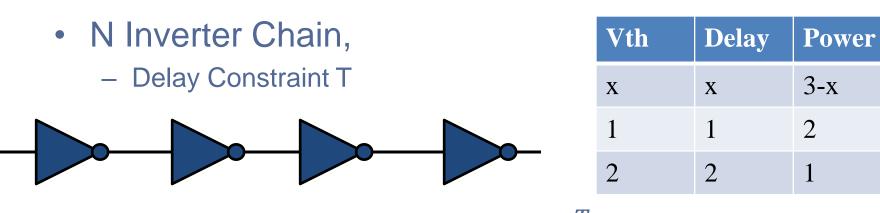
- Experiments and heuristics for selecting library sizes
 - Using Quantization Error + Experimental Results [Beeftink et al 98, 00]

 $so_{Q(SiZe)} = min_{s_i}|s_i - s|$

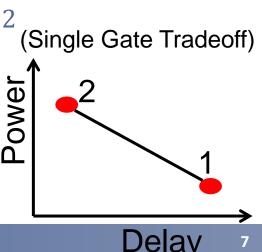
- Experimental Results to determine best library sizes
 - Use the geometric progression 1.3x, $(1.3)^2x$, $(1.3)^3x$, $(1.3)^4x$, etc.
 - [Singhal and Girishankar 06]
 - Use .5x, 1x, 2x, 3x, 4x, 5x
 - [Afonso et al 09]
- Prior art could not predict suboptimality of size selection
 - More difficult and stronger question



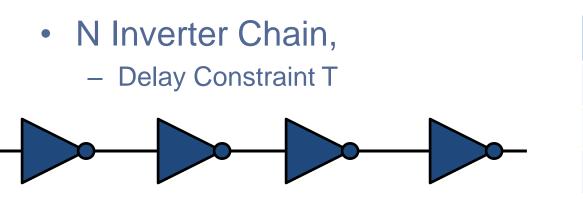
Thought Experiment #1



- Continuous Optimum for $v_{th} = \frac{T}{N}$
- With $v_{th} \in \{1, 2\}$
 - Discrete Optimum: have [T N] gates at $v_{th} = 2$
 - Suboptimality is at most 1
 - Proportional to 1/N & decreases as $N \to \infty$

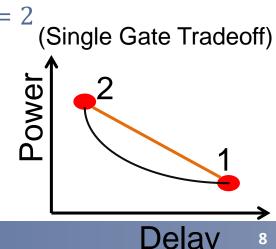


Thought Experiment #2



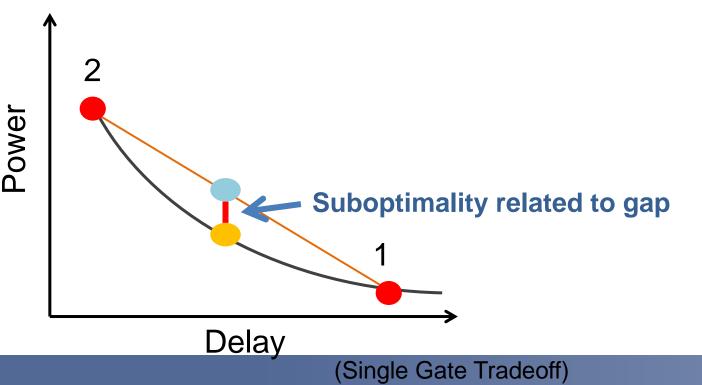


- Same Continuous Optimum: $v_{th} = \frac{T}{N}$
- With $v_{th} \in \{1, 2\}$
 - Discrete Optimum: have [T N] gates at $v_{th} = 2$
 - Suboptimality does not decrease as $N \rightarrow \infty$



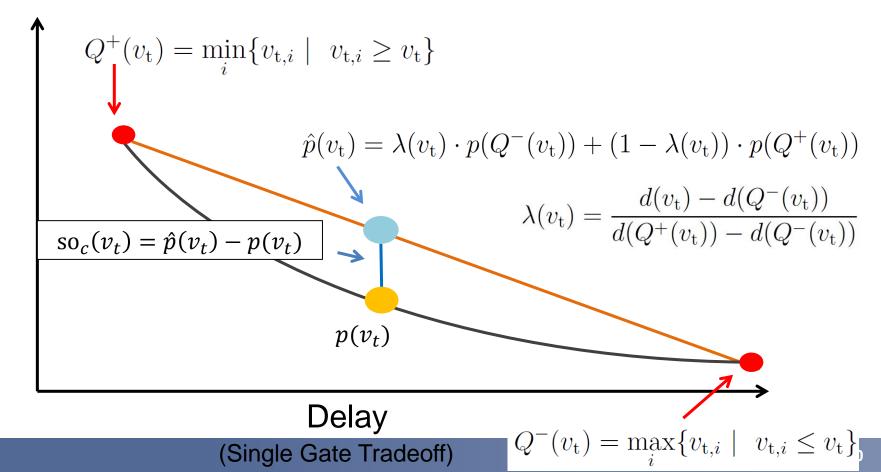
Suboptimality and Convexity

- Power vs. Delay Tradeoff curves are convex nonincreasing functions
- Convex curves have the property that any secant line lies at or above the curve



Suboptimality expressions: vt

• Suboptimality is the difference between the upper line and the lower tradeoff curve



Power

Suboptimality of Full Design

• Sum of individual gate suboptimalities

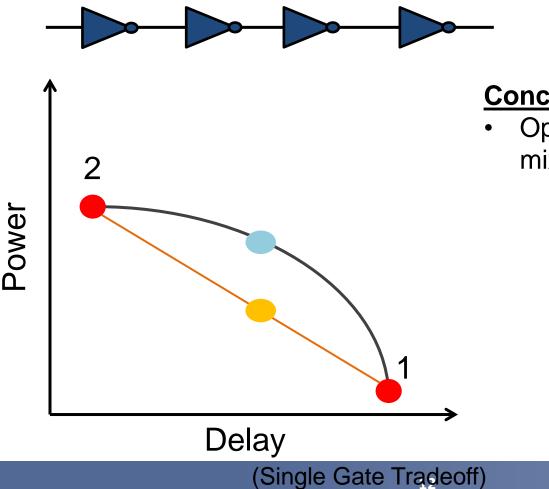
$$so_c(Design) = \sum_{\{\forall g \in Design\}} so_c(v_t)$$

with

 $so_c(v_t) = \hat{p}(v_t) - p(v_t)$: Per gate suboptimality $\hat{p}(v_t)$: Achievable power tradeoff with given sizes $p(v_t)$: Continuous optimal size (v_t) and power $p(v_t)$

Non-convex Power Delay Curves

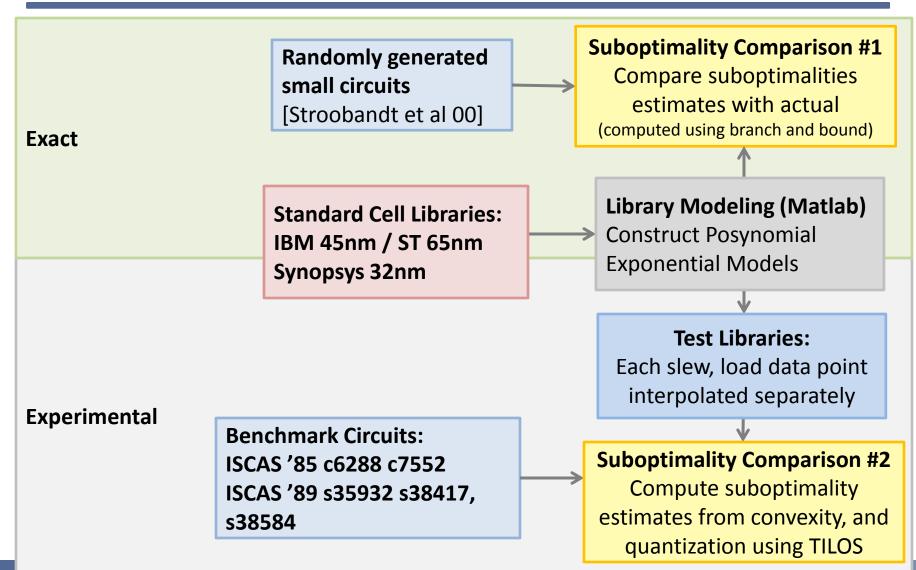
Non-convex curves



Concave Curves

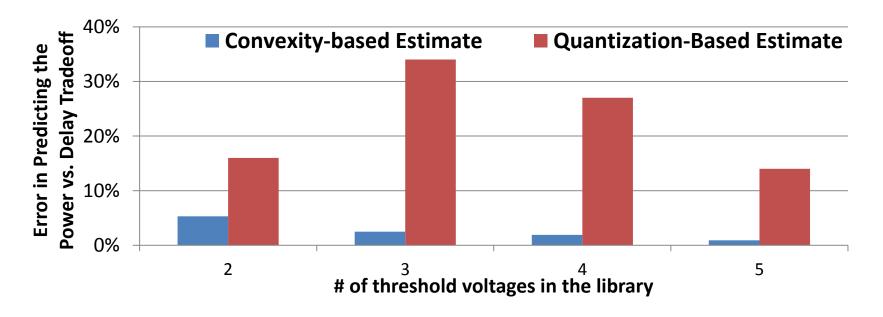
 Optimal Solution Utilizes a mixture of (1) and (2)

Experimental Setup: vt assignment

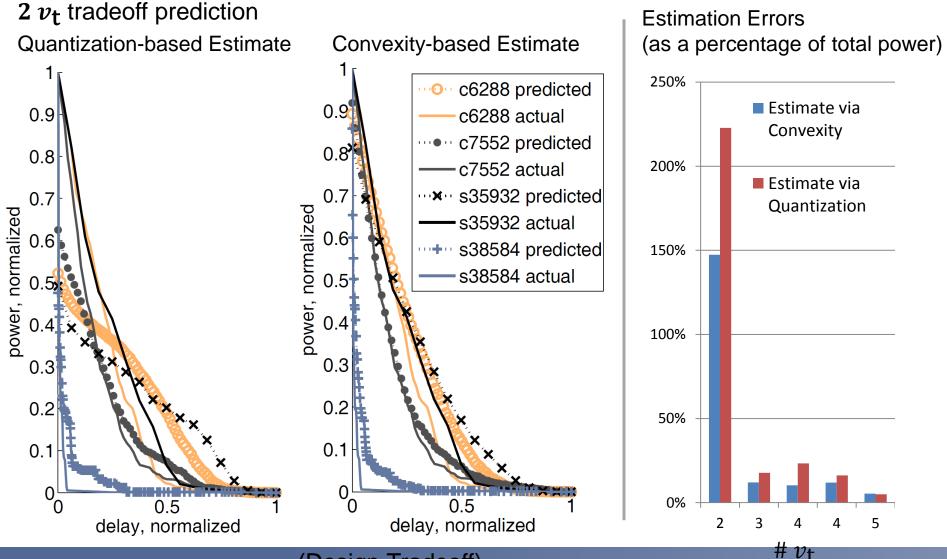


Experiment (Exact Methods): Estimating the tradeoff of v_t assignment

- 30 randomly generated circuits, each with size 30 using [Stroobandt 00]
- Used to predict power delay tradeoff for different v_t libraries



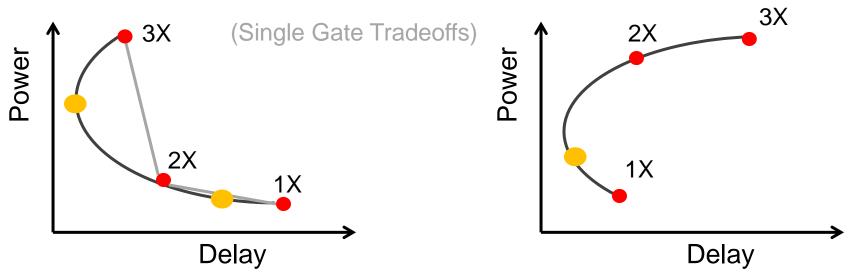
Experiment (TILOS): Estimating the tradeoff of v_t assignment



(Design Tradeoff)

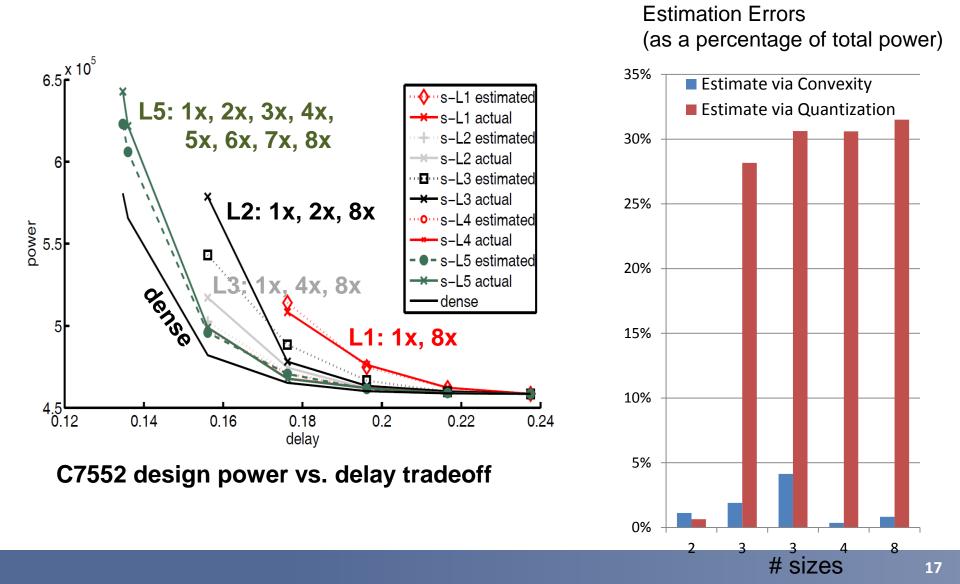
Extension to Gate Sizing

- Power delay curves different for gate sizing
 - Account for both delay at the input and output of the gate



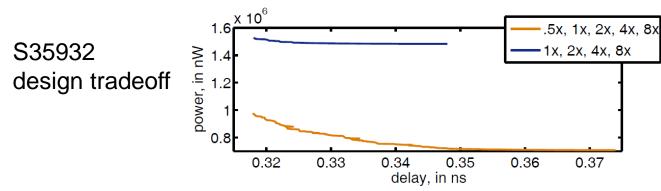
- Two cases:
 - Required delay is **possible** (use the same method as before)
 - Required delay is **impossible** (estimate with **round-up** penalty)
 - Fitting term needed (benchmark dependent)

Experiment: estimating the tradeoff of gate sizing



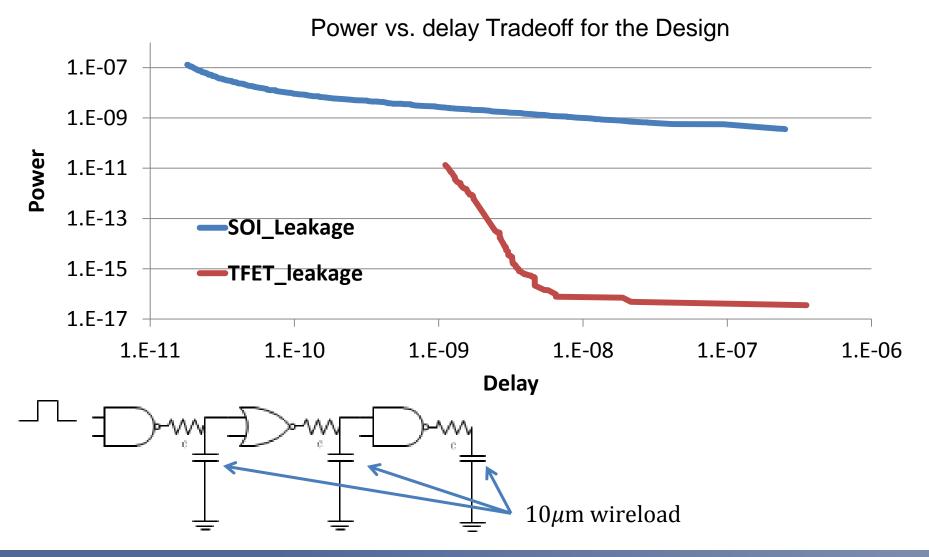
Discussion: Dynamic Range Considerations

- Always need a low power option
 - Dictated by the technology and allowable slew rates



- Estimate as fraction of minimum-sized devices with pos. slack
- Largest Size
 - Related to the capacitive loads in a design
 - Convex p/d curve tradeoff between power vs. delay is worse
- Lowest Vt
 - Related to delay range needs

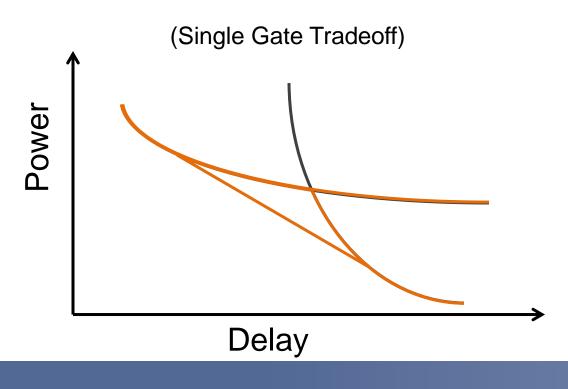
Discussion: SOI and TFET Technology Example



(Data and plot courtesy of Shaodi Wang)

Discussion: Mixing Technologies

- Allows for several tradeoffs:
 - Use one technology
 - Use both technologies but optimize independently
 - Use both technologies and optimize jointly



Summary

- Method to estimate the suboptimality related to a selection of sizes or $v_{\rm f}$
 - Related to the convexity of the power delay tradeoff
- Experimental results show strong explanatory power compared to prior work
 - 2x better (gate sizing) and 10x better (threshold voltage)
 - Use in determining which standard library cells to provide
- Can be used to understand impact of future technologies
 - FinFet Libraries with limited size and vth availability
 - Designs with mixtures of different technologies

References

- R. Afonso, M. Rahman, H. Tennakoon, and C. Sechen. "Power efficient standard cell library design." In *IEEE Dallas Circuits and Systems Workshop, (DCAS)*, pp. 1–4, 2009.
- F. Beeftink, P. Kudva, D. Kung, and L. Stok. "Gate-size selection for standard cell libraries." *In Proc. Int. Conf. Computer-Aided Design*, pp. 545–550, Nov 1998.
- F. Beeftink, P. Kudva, D.S. Kung, R. Puri, and L. Stok. "Combinatorial cell design for CMOS libraries." *Integration, the VLSI Journal*, 29(1):67–93, 2000.
- JP Fishburn and AE Dunlop. "TILOS: A Posynomial Approach to Transistor Sizing." *In Proc. Int. Conf. Computer-Aided Design*, 1985.
- V. Singhal and G. Girishankar. "Optimal Gate Size Selection for Standard Cells in a Library." In IEEE Workshop on Design, Applications, Integration and Software, pp. 47–50, 2006.
- D. Stroobandt, P. Verplaetse, and J. van Campenhout. "Generating synthetic benchmark circuits for evaluating CAD tools," IEEE Trans. on Computer-Aided Design, 19(9):1011 –1022, sep 2000.
- T. Taghavi, C. Alpert, A. Huber, Z. Li, G. Nam, S. Ramji, "New placement prediction and mitigation techniques for local routing congestion," In Proc. Int. Conf. On Computer-Aided Design, Nov. 2010